E·XFL

Renesas Electronics America Inc - R5F100ACDSP#V0 Datasheet

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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Obsolete
Core Processor	RL78
Core Size	16-Bit
Speed	32MHz
Connectivity	CSI, I²C, LINbus, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	21
Program Memory Size	32KB (32K x 8)
Program Memory Type	FLASH
EEPROM Size	4K x 8
RAM Size	2K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 8x8/10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	30-LSSOP (0.240", 6.10mm Width)
Supplier Device Package	30-LSSOP
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f100acdsp-v0

Table 1-1. List of Ordering Part Numbers

(10/12)

Pin count	Package	Data flash	Fields of Application Note	Ordering Part Number
80 pins	80-pin plastic LQFP (14 × 14 mm, 0.65 mm pitch)	Mounted	A	R5F100MFAFA#V0, R5F100MGAFA#V0, R5F100MHAFA#V0, R5F100MJAFA#V0, R5F100MKAFA#V0, R5F100MLAFA#V0 R5F100MFAFA#X0, R5F100MGAFA#X0, R5F100MHAFA#X0, R5F100MJAFA#X0, R5F100MKAFA#X0, R5F100MLAFA#X0
			D	R5F100MFDFA#V0, R5F100MGDFA#V0, R5F100MHDFA#V0, R5F100MJDFA#V0, R5F100MKDFA#V0, R5F100MLDFA#V0 R5F100MFDFA#X0, R5F100MGDFA#X0, R5F100MHDFA#X0, R5F100MJDFA#X0, R5F100MKDFA#X0, R5F100MLDFA#X0
			G	R5F100MFGFA#V0, R5F100MGGFA#V0, R5F100MHGFA#V0, R5F100MJGFA#V0 R5F100MFGFA#X0, R5F100MGGFA#X0, R5F100MHGFA#X0, R5F100MJGFA#X0
		Not mounted	A	R5F101MFAFA#V0, R5F101MGAFA#V0, R5F101MHAFA#V0, R5F101MJAFA#V0, R5F101MKAFA#V0, R5F101MLAFA#V0 R5F101MFAFA#X0, R5F101MGAFA#X0, R5F101MHAFA#X0, R5F101MJAFA#X0, R5F101MKAFA#X0, R5F101MLAFA#X0
			D	R5F101MFDFA#V0, R5F101MGDFA#V0, R5F101MHDFA#V0, R5F101MJDFA#V0, R5F101MKDFA#V0, R5F101MLDFA#V0 R5F101MFDFA#X0, R5F101MGDFA#X0, R5F101MHDFA#X0, R5F101MJDFA#X0, R5F101MKDFA#X0, R5F101MLDFA#X0
	80-pin plastic LFQFP (12 × 12 mm, 0.5 mm pitch)	Mounted	A	R5F100MFAFB#V0, R5F100MGAFB#V0, R5F100MHAFB#V0, R5F100MJAFB#V0, R5F100MKAFB#V0, R5F100MLAFB#V0 R5F100MFAFB#X0, R5F100MGAFB#X0, R5F100MHAFB#X0, R5F100MJAFB#X0, R5F100MKAFB#X0, R5F100MLAFB#X0
			D	R5F100MFDFB#V0, R5F100MGDFB#V0, R5F100MHDFB#V0, R5F100MJDFB#V0, R5F100MKDFB#V0, R5F100MLDFB#V0 R5F100MFDFB#X0, R5F100MGDFB#X0, R5F100MHDFB#X0, R5F100MJDFB#X0, R5F100MKDFB#X0, R5F100MLDFB#X0
			G	R5F100MFGFB#V0, R5F100MGGFB#V0, R5F100MHGFB#V0, R5F100MJGFB#V0 R5F100MFGFB#X0, R5F100MGGFB#X0, R5F100MHGFB#X0, R5F100MJGFB#X0
		Not mounted	A	R5F101MFAFB#V0, R5F101MGAFB#V0, R5F101MHAFB#V0, R5F101MJAFB#V0, R5F101MKAFB#V0, R5F101MLAFB#V0 R5F101MFAFB#X0, R5F101MGAFB#X0, R5F101MHAFB#X0, R5F101MJAFB#X0, R5F101MKAFB#X0, R5F101MLAFB#X0
			D	R5F101MFDFB#V0, R5F101MGDFB#V0, R5F101MHDFB#V0, R5F101MJDFB#V0, R5F101MKDFB#V0, R5F101MLDFB#V0 R5F101MFDFB#X0, R5F101MGDFB#X0, R5F101MHDFB#X0, R5F101MJDFB#X0, R5F101MKDFB#X0, R5F101MLDFB#X0

Note For the fields of application, refer to **Figure 1-1 Part Number, Memory Size, and Package of RL78/G13**.

Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.

Table 1-1. List of Ordering Part Numbers

(12/12)

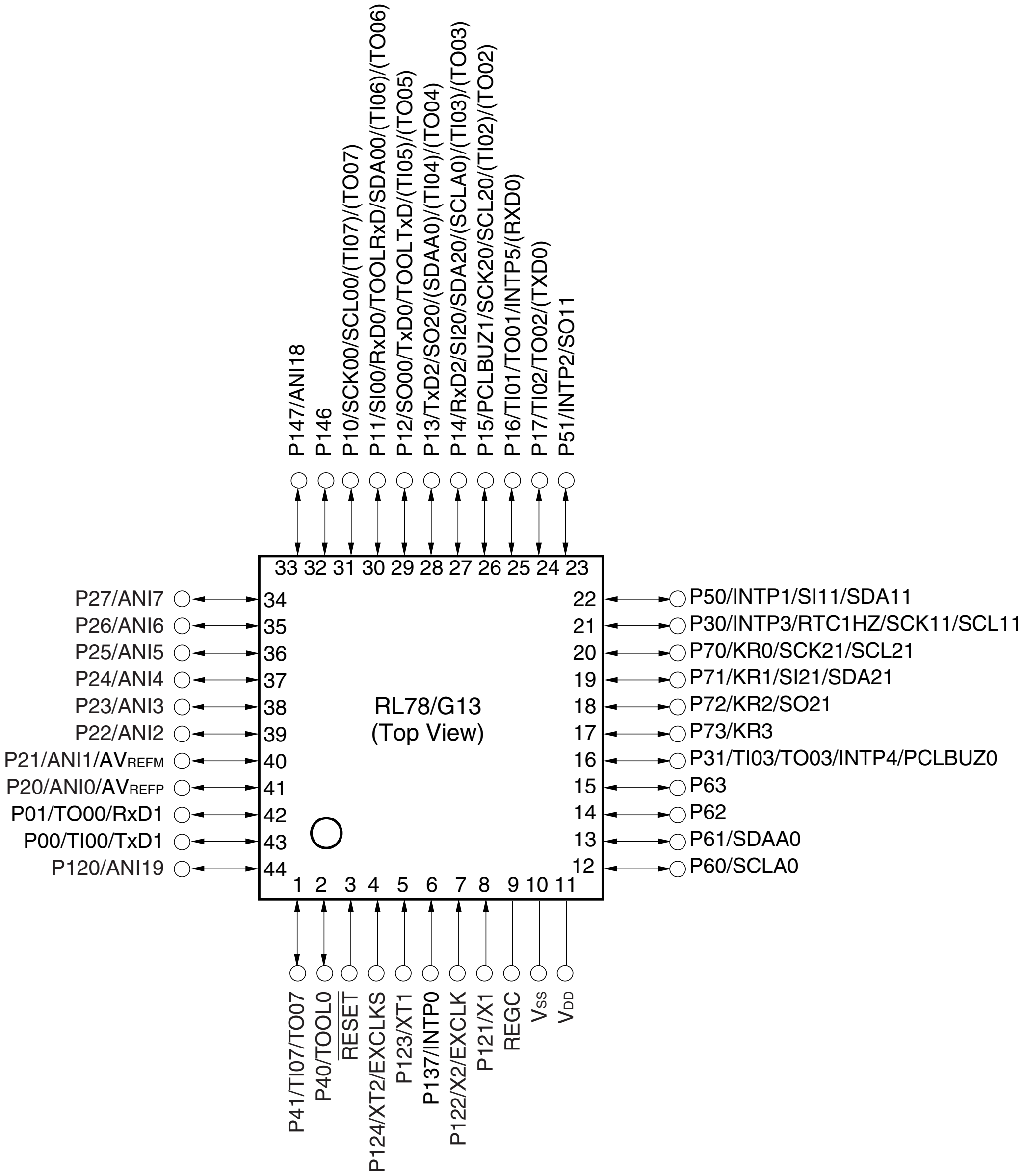
Pin count	Package	Data flash	Fields of Application [Note]	Ordering Part Number
128 pins	128-pin plastic LFQFP (14 × 20 mm, 0.5 mm pitch)	Mounted	A	R5F100SHAFB#V0, R5F100SJAFB#V0, R5F100SKAFB#V0, R5F100SLAFB#V0 R5F100SHAFB#X0, R5F100SJAFB#X0, R5F100SKAFB#X0, R5F100SLAFB#X0
			D	R5F100SHDFB#V0, R5F100SJDFB#V0, R5F100SKDFB#V0, R5F100SLDFB#V0 R5F100SHDFB#X0, R5F100SJDFB#X0, R5F100SKDFB#X0, R5F100SLDFB#X0
		Not mounted	A	R5F101SHAFB#V0, R5F101SJAFB#V0, R5F101SKAFB#V0, R5F101SLAFB#V0 R5F101SHAFB#X0, R5F101SJAFB#X0, R5F101SKAFB#X0, R5F101SLAFB#X0
			D	R5F101SHDFB#V0, R5F101SJDFB#V0, R5F101SKDFB#V0, R5F101SLDFB#V0 R5F101SHDFB#X0, R5F101SJDFB#X0, R5F101SKDFB#X0, R5F101SLDFB#X0

Note For the fields of application, refer to **Figure 1-1 Part Number, Memory Size, and Package of RL78/G13**.

Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.

1.3.8 44-pin products

- 44-pin plastic LQFP (10 × 10 mm, 0.8 mm pitch)

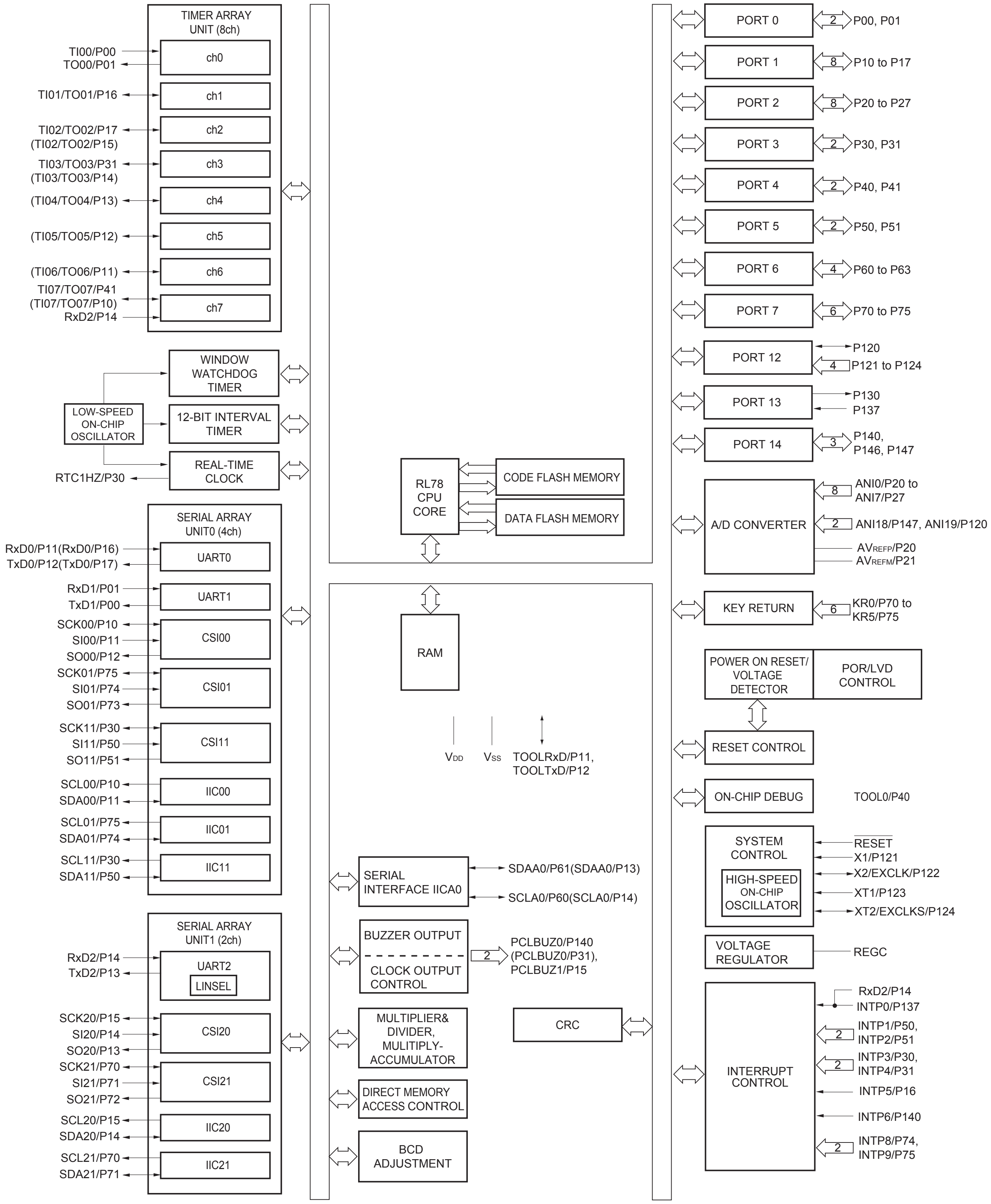


Caution Connect the REGC pin to Vss via a capacitor (0.47 to 1 μF).

Remarks 1. For pin identification, see **1.4 Pin Identification**.

2. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to **Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR)** in the RL78/G13 User's Manual.

1.5.9 48-pin products



Remark Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to **Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR)** in the RL78/G13 User's Manual.

2. ELECTRICAL SPECIFICATIONS (T_A = -40 to +85°C)

This chapter describes the following electrical specifications.

Target products A: Consumer applications T_A = −40 to +85°C
R5F100xxAxx, R5F101xxAxx
D: Industrial applications T_A = −40 to +85°C
R5F100xxDxx, R5F101xxDxx
G: Industrial applications when T_A = −40 to +105°C products is used in the range of T_A = −40 to +85°C
R5F100xxGxx

Cautions 1. The RL78 microcontrollers have an on-chip debug function, which is provided for development and evaluation. Do not use the on-chip debug function in products designated for mass production, because the guaranteed number of rewritable times of the flash memory may be exceeded when this function is used, and product reliability therefore cannot be guaranteed. Renesas Electronics is not liable for problems occurring when the on-chip debug function is used.

2. With products not provided with an EV_{DD0}, EV_{DD1}, EV_{SS0}, or EV_{SS1} pin, replace EV_{DD0} and EV_{DD1} with V_{DD}, or replace EV_{SS0} and EV_{SS1} with V_{SS}.

3. The pins mounted depend on the product. Refer to 2.1 Port Function to 2.2.1 Functions for each product.

($T_A = -40$ to $+85°C$, $1.6\ V \leq EV_{DD0} = EV_{DD1} \leq V_{DD} \leq 5.5\ V$, $V_{SS} = EV_{SS0} = EV_{SS1} = 0\ V$) (4/5)

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output voltage, high	V_{OH1}	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147	$4.0\ V \leq EV_{DD0} \leq 5.5\ V$, $I_{OH1} = -10.0\ mA$	$EV_{DD0} - 1.5$			V
			$4.0\ V \leq EV_{DD0} \leq 5.5\ V$, $I_{OH1} = -3.0\ mA$	$EV_{DD0} - 0.7$			V
			$2.7\ V \leq EV_{DD0} \leq 5.5\ V$, $I_{OH1} = -2.0\ mA$	$EV_{DD0} - 0.6$			V
			$1.8\ V \leq EV_{DD0} \leq 5.5\ V$, $I_{OH1} = -1.5\ mA$	$EV_{DD0} - 0.5$			V
			$1.6\ V \leq EV_{DD0} < 5.5\ V$, $I_{OH1} = -1.0\ mA$	$EV_{DD0} - 0.5$			V
	V_{OH2}	P20 to P27, P150 to P156	$1.6\ V \leq V_{DD} \leq 5.5\ V$, $I_{OH2} = -100\ \mu A$	$V_{DD} - 0.5$			V
Output voltage, low	V_{OL1}	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147	$4.0\ V \leq EV_{DD0} \leq 5.5\ V$, $I_{OL1} = 20\ mA$			1.3	V
			$4.0\ V \leq EV_{DD0} \leq 5.5\ V$, $I_{OL1} = 8.5\ mA$			0.7	V
			$2.7\ V \leq EV_{DD0} \leq 5.5\ V$, $I_{OL1} = 3.0\ mA$			0.6	V
			$2.7\ V \leq EV_{DD0} \leq 5.5\ V$, $I_{OL1} = 1.5\ mA$			0.4	V
			$1.8\ V \leq EV_{DD0} \leq 5.5\ V$, $I_{OL1} = 0.6\ mA$			0.4	V
			$1.6\ V \leq EV_{DD0} < 5.5\ V$, $I_{OL1} = 0.3\ mA$			0.4	V
	V_{OL2}	P20 to P27, P150 to P156	$1.6\ V \leq V_{DD} \leq 5.5\ V$, $I_{OL2} = 400\ \mu A$			0.4	V
	V_{OL3}	P60 to P63	$4.0\ V \leq EV_{DD0} \leq 5.5\ V$, $I_{OL3} = 15.0\ mA$			2.0	V
			$4.0\ V \leq EV_{DD0} \leq 5.5\ V$, $I_{OL3} = 5.0\ mA$			0.4	V
			$2.7\ V \leq EV_{DD0} \leq 5.5\ V$, $I_{OL3} = 3.0\ mA$			0.4	V
			$1.8\ V \leq EV_{DD0} \leq 5.5\ V$, $I_{OL3} = 2.0\ mA$			0.4	V
			$1.6\ V \leq EV_{DD0} < 5.5\ V$, $I_{OL3} = 1.0\ mA$			0.4	V

Caution P00, P02 to P04, P10 to P15, P17, P43 to P45, P50, P52 to P55, P71, P74, P80 to P82, P96, and P142 to P144 do not output high level in N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

(T_A = –40 to +85°C, 1.6 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V) (5/5)

Items	Symbol	Conditions			MIN.	TYP.	MAX.	Unit
Input leakage current, high	I_{LIH1}	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P140 to P147	V_I = EV_{DD0}				1	μA
	I_{LIH2}	P20 to P27, P137, P150 to P156, $\overline{RESET}$	V_I = V_{DD}				1	μA
	I_{LIH3}	P121 to P124 (X1, X2, XT1, XT2, EXCLK, EXCLKS)	V_I = V_{DD}	In input port or external clock input			1	μA
				In resonator connection			10	μA
Input leakage current, low	I_{LIL1}	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P140 to P147	V_I = EV_{SS0}				–1	μA
	I_{LIL2}	P20 to P27, P137, P150 to P156, $\overline{RESET}$	V_I = V_{SS}				–1	μA
	I_{LIL3}	P121 to P124 (X1, X2, XT1, XT2, EXCLK, EXCLKS)	V_I = V_{SS}	In input port or external clock input			–1	μA
				In resonator connection			–10	μA
On-chip pll-up resistance	R_U	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P140 to P147	V_I = EV_{SS0}, In input port		10	20	100	kΩ

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

(2) Flash ROM: 96 to 256 KB of 30- to 100-pin products

(T_A = −40 to +85°C, 1.6 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V) (2/2)

Parameter	Symbol	Conditions				MIN.	TYP.	MAX.	Unit
Supply current [Note 1]	I_{DD2} [Note 2]	HALT mode	HS (high-speed main) mode [Note 7]	f_{IH} = 32 MHz [Note 4]	V_{DD} = 5.0 V		0.62	1.86	mA
					V_{DD} = 3.0 V		0.62	1.86	mA
				f_{IH} = 24 MHz [Note 4]	V_{DD} = 5.0 V		0.50	1.45	mA
					V_{DD} = 3.0 V		0.50	1.45	mA
				f_{IH} = 16 MHz [Note 4]	V_{DD} = 5.0 V		0.44	1.11	mA
					V_{DD} = 3.0 V		0.44	1.11	mA
			LS (low-speed main) mode [Note 7]	f_{IH} = 8 MHz [Note 4]	V_{DD} = 3.0 V		290	620	μA
					V_{DD} = 2.0 V		290	620	μA
			LV (low-voltage main) mode [Note 7]	f_{IH} = 4 MHz [Note 4]	V_{DD} = 3.0 V		440	680	μA
					V_{DD} = 2.0 V		440	680	μA
			HS (high-speed main) mode [Note 7]	f_{MX} = 20 MHz [Note 3], V_{DD} = 5.0 V	Square wave input		0.31	1.08	mA
					Resonator connection		0.48	1.28	mA
				f_{MX} = 20 MHz [Note 3], V_{DD} = 3.0 V	Square wave input		0.31	1.08	mA
					Resonator connection		0.48	1.28	mA
				f_{MX} = 10 MHz [Note 3], V_{DD} = 5.0 V	Square wave input		0.21	0.63	mA
					Resonator connection		0.28	0.71	mA
				f_{MX} = 10 MHz [Note 3], V_{DD} = 3.0 V	Square wave input		0.21	0.63	mA
					Resonator connection		0.28	0.71	mA
			LS (low-speed main) mode [Note 7]	f_{MX} = 8 MHz [Note 3], V_{DD} = 3.0 V	Square wave input		110	360	μA
					Resonator connection		160	420	μA
				f_{MX} = 8 MHz [Note 3], V_{DD} = 2.0 V	Square wave input		110	360	μA
					Resonator connection		160	420	μA
			Subsystem clock operation	f_{SUB} = 32.768 kHz [Note 5] T_A = −40°C	Square wave input		0.28	0.61	μA
					Resonator connection		0.47	0.80	μA
				f_{SUB} = 32.768 kHz [Note 5] T_A = +25°C	Square wave input		0.34	0.61	μA
					Resonator connection		0.53	0.80	μA
				f_{SUB} = 32.768 kHz [Note 5] T_A = +50°C	Square wave input		0.41	2.30	μA
					Resonator connection		0.60	2.49	μA
				f_{SUB} = 32.768 kHz [Note 5] T_A = +70°C	Square wave input		0.64	4.03	μA
					Resonator connection		0.83	4.22	μA
				f_{SUB} = 32.768 kHz [Note 5] T_A = +85°C	Square wave input		1.09	8.04	μA
					Resonator connection		1.28	8.23	μA
	I_{DD3} [Note 6]	STOP mode [Note 8]	T_A = −40°C				0.19	0.52	μA
			T_A = +25°C				0.25	0.52	μA
			T_A = +50°C				0.32	2.21	μA
			T_A = +70°C				0.55	3.94	μA
			T_A = +85°C				1.00	7.95	μA

(**Notes** and **Remarks** are listed on the next page.)

Remarks 1. p: CSI number (p = 00, 01, 10, 11, 20, 21, 30, 31), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3),
g: PIM and POM numbers (g = 0, 1, 4, 5, 8, 14)

2. f_{MCK}: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13))

(4) During communication at same potential (CSI mode) (slave mode, SCKp... external clock input) (1/2)

(T_A = –40 to +85°C, 1.6 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time Note 5	t_{KCY2}	4.0 V ≤ EV_{DD0} ≤ 5.5 V	20 MHz < f_{MCK}	8/f_{MCK}		—		—		ns
			f_{MCK} ≤ 20 MHz	6/f_{MCK}		6/f_{MCK}		6/f_{MCK}		ns
		2.7 V ≤ EV_{DD0} ≤ 5.5 V	16 MHz < f_{MCK}	8/f_{MCK}		—		—		ns
			f_{MCK} ≤ 16 MHz	6/f_{MCK}		6/f_{MCK}		6/f_{MCK}		ns
		2.4 V ≤ EV_{DD0} ≤ 5.5 V		6/f_{MCK} and 500		6/f_{MCK} and 500		6/f_{MCK} and 500		ns
		1.8 V ≤ EV_{DD0} ≤ 5.5 V		6/f_{MCK} and 750		6/f_{MCK} and 750		6/f_{MCK} and 750		ns
		1.7 V ≤ EV_{DD0} ≤ 5.5 V		6/f_{MCK} and 1500		6/f_{MCK} and 1500		6/f_{MCK} and 1500		ns
		1.6 V ≤ EV_{DD0} ≤ 5.5 V		—		6/f_{MCK} and 1500		6/f_{MCK} and 1500		ns
SCKp high-/low-level width	t_{KH2}, t_{KL2}	4.0 V ≤ EV_{DD0} ≤ 5.5 V		t_{KCY2}/2 – 7		t_{KCY2}/2 – 7		t_{KCY2}/2 – 7		ns
		2.7 V ≤ EV_{DD0} ≤ 5.5 V		t_{KCY2}/2 – 8		t_{KCY2}/2 – 8		t_{KCY2}/2 – 8		ns
		1.8 V ≤ EV_{DD0} ≤ 5.5 V		t_{KCY2}/2 – 18		t_{KCY2}/2 – 18		t_{KCY2}/2 – 18		ns
		1.7 V ≤ EV_{DD0} ≤ 5.5 V		t_{KCY2}/2 – 66		t_{KCY2}/2 – 66		t_{KCY2}/2 – 66		ns
		1.6 V ≤ EV_{DD0} ≤ 5.5 V		—		t_{KCY2}/2 – 66		t_{KCY2}/2 – 66		ns

(**Notes**, **Caution**, and **Remarks** are listed on the next page.)

(7) Communication at different potential (2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output, corresponding CSI00 only) (2/2)

($T_A = -40$ to $+85°C$, $2.7\text{ V} \leq EV_{DD0} = EV_{DD1} \leq V_{DD} \leq 5.5\text{ V}$, $V_{SS} = EV_{SS0} = EV_{SS1} = 0\text{ V}$)

Parameter	Symbol	Conditions	HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SIp setup time (to SCKp↓) Note 2	t_{SIK1}	$4.0\text{ V} \leq EV_{DD0} \leq 5.5\text{ V}$, $2.7\text{ V} \leq V_b \leq 4.0\text{ V}$, $C_b = 20\text{ pF}$, $R_b = 1.4\text{ k}\Omega$	23		110		110		ns
		$2.7\text{ V} \leq EV_{DD0} < 4.0\text{ V}$, $2.3\text{ V} \leq V_b \leq 2.7\text{ V}$, $C_b = 20\text{ pF}$, $R_b = 2.7\text{ k}\Omega$	33		110		110		ns
SIp hold time (from SCKp↓) Note 2	t_{KSI1}	$4.0\text{ V} \leq EV_{DD0} \leq 5.5\text{ V}$, $2.7\text{ V} \leq V_b \leq 4.0\text{ V}$, $C_b = 20\text{ pF}$, $R_b = 1.4\text{ k}\Omega$	10		10		10		ns
		$2.7\text{ V} \leq EV_{DD0} < 4.0\text{ V}$, $2.3\text{ V} \leq V_b \leq 2.7\text{ V}$, $C_b = 20\text{ pF}$, $R_b = 2.7\text{ k}\Omega$	10		10		10		ns
Delay time from SCKp↑ to SOp output Note 2	t_{KSO1}	$4.0\text{ V} \leq EV_{DD0} \leq 5.5\text{ V}$, $2.7\text{ V} \leq V_b \leq 4.0\text{ V}$, $C_b = 20\text{ pF}$, $R_b = 1.4\text{ k}\Omega$		10		10		10	ns
		$2.7\text{ V} \leq EV_{DD0} < 4.0\text{ V}$, $2.3\text{ V} \leq V_b \leq 2.7\text{ V}$, $C_b = 20\text{ pF}$, $R_b = 2.7\text{ k}\Omega$		10		10		10	ns

Notes **1.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.

2. When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (V_{DD} tolerance (When 20- to 52-pin products)/EV_{DD} tolerance (When 64- to 128-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

Remarks **1.** $R_b[\Omega]$:Communication line (SCKp, SOp) pull-up resistance, C_b[F]: Communication line (SCKp, SOp) load capacitance, V_b[V]: Communication line voltage

2. p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0),
g: PIM and POM number (g = 1)

3. f_{MCK}: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00))

4. This value is valid only when CSI00's peripheral I/O redirect function is not used.

(8) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output) (2/3)

(T_A = −40 to +85°C, 1.8 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V)

Parameter	Symbol	Conditions	HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SIp setup time (to SCKp↑) Note 1	t_{SIK1}	4.0 V ≤ EV_{DD0} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 30 pF, R_b = 1.4 kΩ	81		479		479		ns
		2.7 V ≤ EV_{DD0} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ	177		479		479		ns
		1.8 V ≤ EV_{DD0} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 2, C_b = 30 pF, R_b = 5.5 kΩ	479		479		479		ns
SIp hold time (from SCKp↑) Note 1	t_{KSI1}	4.0 V ≤ EV_{DD0} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 30 pF, R_b = 1.4 kΩ	19		19		19		ns
		2.7 V ≤ EV_{DD0} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ	19		19		19		ns
		1.8 V ≤ EV_{DD0} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 2, C_b = 30 pF, R_b = 5.5 kΩ	19		19		19		ns
Delay time from SCKp↓ to SOp output Note 1	t_{KSO1}	4.0 V ≤ EV_{DD0} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 30 pF, R_b = 1.4 kΩ		100		100		100	ns
		2.7 V ≤ EV_{DD0} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ		195		195		195	ns
		1.8 V ≤ EV_{DD0} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 2, C_b = 30 pF, R_b = 5.5 kΩ		483		483		483	ns

Notes

1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.
2. Use it with EV_{DD0} ≥ V_b.

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (V_{DD} tolerance (When 20- to 52-pin products)/EV_{DD} tolerance (When 64- to 128-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

(**Remarks** are listed on the page after the next page.)

(8) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output) (3/3)

(T_A = –40 to +85°C, 1.8 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V)

Parameter	Symbol	Conditions	HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SIp setup time (to SCKp↓) Note 1	t_{SIK1}	4.0 V ≤ EV_{DD0} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 30 pF, R_b = 1.4 kΩ	44		110		110		ns
		2.7 V ≤ EV_{DD0} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ	44		110		110		ns
		1.8 V ≤ EV_{DD0} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 2, C_b = 30 pF, R_b = 5.5 kΩ	110		110		110		ns
SIp hold time (from SCKp↓) Note 1	t_{KSI1}	4.0 V ≤ EV_{DD0} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 30 pF, R_b = 1.4 kΩ	19		19		19		ns
		2.7 V ≤ EV_{DD0} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ	19		19		19		ns
		1.8 V ≤ EV_{DD0} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 2, C_b = 30 pF, R_b = 5.5 kΩ	19		19		19		ns
Delay time from SCKp↑ to SOp output Note 1	t_{KSO1}	4.0 V ≤ EV_{DD0} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 30 pF, R_b = 1.4 kΩ		25		25		25	ns
		2.7 V ≤ EV_{DD0} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ		25		25		25	ns
		1.8 V ≤ EV_{DD0} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 2, C_b = 30 pF, R_b = 5.5 kΩ		25		25		25	ns

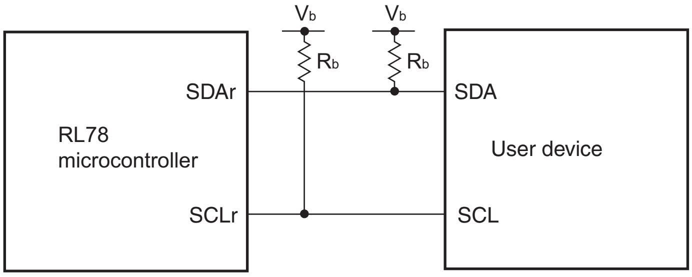
Notes **1.** When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

2. Use it with EV_{DD0} ≥ V_b.

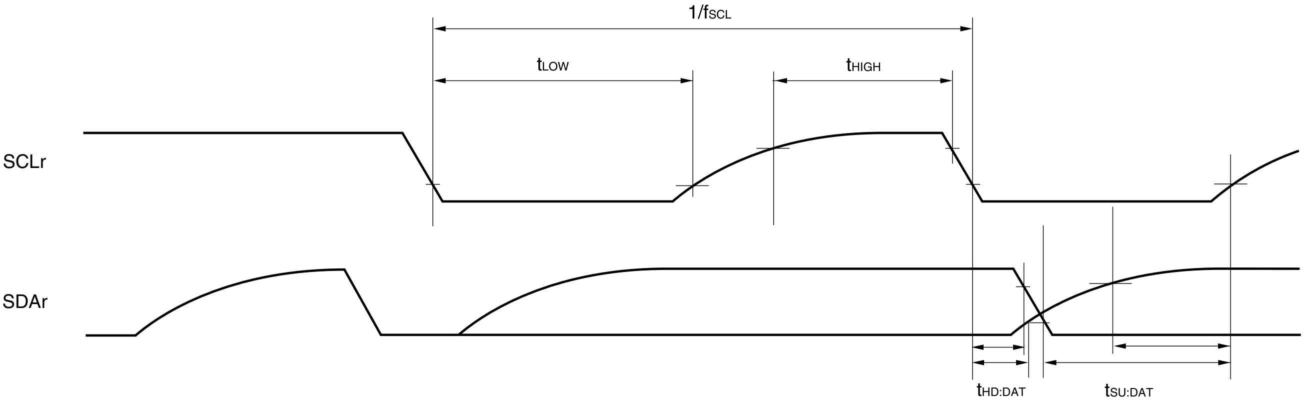
Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (V_{DD} tolerance (When 20- to 52-pin products)/EV_{DD} tolerance (When 64- to 128-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

(**Remarks** are listed on the next page.)

Simplified I²C mode connection diagram (during communication at different potential)



Simplified I²C mode serial transfer timing (during communication at different potential)



Remarks 1. R_b[Ω]:Communication line (SDAr, SCLr) pull-up resistance, C_b[F]: Communication line (SDAr, SCLr) load capacitance, V_b[V]: Communication line voltage

2. r: IIC number (r = 00, 01, 10, 20, 30, 31), g: PIM, POM number (g = 0, 1, 4, 5, 8, 14)

3. f_{MCK}: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00, 01, 02, 10, 12, 13)

(4) When reference voltage (+) = Internal reference voltage (ADREFP1 = 1, ADREFP0 = 0), reference voltage (–) = AV_{REFM}/ANI1 (ADREFM = 1), target pin : ANI0, ANI2 to ANI14, ANI16 to ANI26

(T_A = –40 to +85°C, 2.4 V ≤ V_{DD} ≤ 5.5 V, 1.6 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD}, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V, Reference voltage (+) = V_{BGR} [Note 3], Reference voltage (–) = AV_{REFM} = 0 V [Note 4], HS (high-speed main) mode)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES				8		bit
Conversion time	t_{CONV}	8-bit resolution	2.4 V ≤ V_{DD} ≤ 5.5 V	17		39	μs
Zero-scale error [Notes 1, 2]	E_{ZS}	8-bit resolution	2.4 V ≤ V_{DD} ≤ 5.5 V			±0.60	%FSR
Integral linearity error [Note 1]	ILE	8-bit resolution	2.4 V ≤ V_{DD} ≤ 5.5 V			±2.0	LSB
Differential linearity error [Note 1]	DLE	8-bit resolution	2.4 V ≤ V_{DD} ≤ 5.5 V			±1.0	LSB
Analog input voltage	V_{AIN}			0		V_{BGR} [Note 3]	V

Notes 1. Excludes quantization error (±1/2 LSB).

2. This value is indicated as a ratio (%FSR) to the full-scale value.

3. Refer to **2.6.2 Temperature sensor/internal reference voltage characteristics**.

4. When reference voltage (–) = V_{SS}, the MAX. values are as follows.
Zero-scale error: Add ±0.35%FSR to the MAX. value when reference voltage (–) = AV_{REFM}.
Integral linearity error: Add ±0.5 LSB to the MAX. value when reference voltage (–) = AV_{REFM}.
Differential linearity error: Add ±0.2 LSB to the MAX. value when reference voltage (–) = AV_{REFM}.

(T_A = −40 to +105°C, 2.4 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V) (4/5)

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output voltage, high	V_{OH1}	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147	4.0 V ≤ EV_{DD0} ≤ 5.5 V, I_{OH1} = −3.0 mA	EV_{DD0} − 0.7			V
			2.7 V ≤ EV_{DD0} ≤ 5.5 V, I_{OH1} = −2.0 mA	EV_{DD0} − 0.6			V
			2.4 V ≤ EV_{DD0} ≤ 5.5 V, I_{OH1} = −1.5 mA	EV_{DD0} − 0.5			V
	V_{OH2}	P20 to P27, P150 to P156	2.4 V ≤ V_{DD} ≤ 5.5 V, I_{OH2} = −100 μA	V_{DD} − 0.5			V
Output voltage, low	V_{OL1}	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147	4.0 V ≤ EV_{DD0} ≤ 5.5 V, I_{OL1} = 8.5 mA			0.7	V
			4.0 V ≤ EV_{DD0} ≤ 5.5 V, I_{OL1} = 3.0 mA			0.6	V
			2.7 V ≤ EV_{DD0} ≤ 5.5 V, I_{OL1} = 1.5 mA			0.4	V
			2.4 V ≤ EV_{DD0} ≤ 5.5 V, I_{OL1} = 0.6 mA			0.4	V
	V_{OL2}	P20 to P27, P150 to P156	2.4 V ≤ V_{DD} ≤ 5.5 V, I_{OL2} = 400 μA			0.4	V
	V_{OL3}	P60 to P63	4.0 V ≤ EV_{DD0} ≤ 5.5 V, I_{OL3} = 15.0 mA			2.0	V
			4.0 V ≤ EV_{DD0} ≤ 5.5 V, I_{OL3} = 5.0 mA			0.4	V
			2.7 V ≤ EV_{DD0} ≤ 5.5 V, I_{OL3} = 3.0 mA			0.4	V
			2.4 V ≤ EV_{DD0} ≤ 5.5 V, I_{OL3} = 2.0 mA			0.4	V

Caution **P00, P02 to P04, P10 to P15, P17, P43 to P45, P50, P52 to P55, P71, P74, P80 to P82, P96, and P142 to P144 do not output high level in N-ch open-drain mode.**

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

Notes 1. Total current flowing into V_{DD} and EV_{DD0}, including the input leakage current flowing when the level of the input pin is fixed to V_{DD}, EV_{DD0} or V_{SS}, EV_{SS0}. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.

2. When high-speed on-chip oscillator and subsystem clock are stopped.

3. When high-speed system clock and subsystem clock are stopped.

4. When high-speed on-chip oscillator and high-speed system clock are stopped. When AMPHS1 = 1 (Ultra-low power consumption oscillation). However, not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer.

5. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

HS (high-speed main) mode: $2.7 \text{ V} \leq V_{DD} \leq 5.5 \text{ V}$@1 MHz to 32 MHz
$2.4 \text{ V} \leq V_{DD} \leq 5.5 \text{ V}$@1 MHz to 16 MHz

Remarks 1. f_{MX}: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)

2. f_{IH}: High-speed on-chip oscillator clock frequency

3. f_{SUB}: Subsystem clock frequency (XT1 clock oscillation frequency)

4. Except subsystem clock operation, temperature condition of the TYP. value is T_A = 25°C

(8) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I^2C mode) (2/2)

(T_A = –40 to +105°C, 2.4 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V)

Parameter	Symbol	Conditions	HS (high-speed main) Mode		Unit
			MIN.	MAX.	
Data setup time (reception)	$t_{SU:DAT}$	4.0 V ≤ EV_{DD0} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 50 pF, R_b = 2.7 kΩ	1/f_{MCK} + 340 Note 2		ns
		2.7 V ≤ EV_{DD0} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 50 pF, R_b = 2.7 kΩ	1/f_{MCK} + 340 Note 2		ns
		4.0 V ≤ EV_{DD0} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 100 pF, R_b = 2.8 kΩ	1/f_{MCK} + 760 Note 2		ns
		2.7 V ≤ EV_{DD0} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 100 pF, R_b = 2.7 kΩ	1/f_{MCK} + 760 Note 2		ns
		2.4 V ≤ EV_{DD0} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V, C_b = 100 pF, R_b = 5.5 kΩ	1/f_{MCK} + 570 Note 2		ns
Data hold time (transmission)	$t_{HD:DAT}$	4.0 V ≤ EV_{DD0} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 50 pF, R_b = 2.7 kΩ	0	770	ns
		2.7 V ≤ EV_{DD0} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 50 pF, R_b = 2.7 kΩ	0	770	ns
		4.0 V ≤ EV_{DD0} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 100 pF, R_b = 2.8 kΩ	0	1420	ns
		2.7 V ≤ EV_{DD0} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 100 pF, R_b = 2.7 kΩ	0	1420	ns
		2.4 V ≤ EV_{DD0} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V, C_b = 100 pF, R_b = 5.5 kΩ	0	1215	ns

Notes 1. The value must also be equal to or less than f_{MCK}/4.

2. Set the f_{MCK} value to keep the hold time of SCLr = "L" and SCLr = "H".

Caution Select the TTL input buffer and the N-ch open drain output (V_{DD} tolerance (for the 20- to 52-pin products)/EV_{DD} tolerance (for the 64- to 100-pin products)) mode for the SDAr pin and the N-ch open drain output (V_{DD} tolerance (for the 20- to 52-pin products)/EV_{DD} tolerance (for the 64- to 100-pin products)) mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

(**Remarks** are listed on the next page.)

(3) When reference voltage (+) = V_{DD} (ADREFP1 = 0, ADREFP0 = 0), reference voltage (–) = V_{SS} (ADREFM = 0), target pin : ANI0 to ANI14, ANI16 to ANI26, internal reference voltage, and temperature sensor output voltage

(T_A = –40 to +105°C, 2.4 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V, Reference voltage (+) = V_{DD}, Reference voltage (–) = V_{SS})

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error[Note 1]	AINL	10-bit resolution	2.4 V ≤ V_{DD} ≤ 5.5 V		1.2	±7.0	LSB
Conversion time	t_{CONV}	10-bit resolution Target pin: ANI0 to ANI14, ANI16 to ANI26	3.6 V ≤ V_{DD} ≤ 5.5 V	2.125		39	μs
			2.7 V ≤ V_{DD} ≤ 5.5 V	3.1875		39	μs
			2.4 V ≤ V_{DD} ≤ 5.5 V	17		39	μs
		10-bit resolution Target pin: Internal reference voltage, and temperature sensor output voltage (HS (high-speed main) mode)	3.6 V ≤ V_{DD} ≤ 5.5 V	2.375		39	μs
			2.7 V ≤ V_{DD} ≤ 5.5 V	3.5625		39	μs
			2.4 V ≤ V_{DD} ≤ 5.5 V	17		39	μs
Zero-scale error[Notes 1, 2]	E_{ZS}	10-bit resolution	2.4 V ≤ V_{DD} ≤ 5.5 V			±0.60	%FSR
Full-scale error[Notes 1, 2]	E_{FS}	10-bit resolution	2.4 V ≤ V_{DD} ≤ 5.5 V			±0.60	%FSR
Integral linearity error[Note 1]	ILE	10-bit resolution	2.4 V ≤ V_{DD} ≤ 5.5 V			±4.0	LSB
Differential linearity error[Note 1]	DLE	10-bit resolution	2.4 V ≤ V_{DD} ≤ 5.5 V			±2.0	LSB
Analog input voltage	V_{AIN}	ANI0 to ANI14		0		V_{DD}	V
		ANI16 to ANI26		0		EV_{DD0}	V
		Internal reference voltage output (2.4 V ≤ V_{DD} ≤ 5.5 V, HS (high-speed main) mode)		V_{BGR}[Note 3]			V
		Temperature sensor output voltage (2.4 V ≤ V_{DD} ≤ 5.5 V, HS (high-speed main) mode)		V_{TMPS25}[Note 3]			V

Notes
1. Excludes quantization error (±1/2 LSB).
2. This value is indicated as a ratio (%FSR) to the full-scale value.
3. Refer to **3.6.2 Temperature sensor/internal reference voltage characteristics**.

R5F100LCABG, R5F100LDABG, R5F100LEABG, R5F100LFABG, R5F100LGABG, R5F100LHABG, R5F100LJABG

R5F101LCABG, R5F101LDABG, R5F101LEABG, R5F101LFABG, R5F101LGABG, R5F101LHABG, R5F101LJABG

R5F100LCGBG, R5F100LDGBG, R5F100LEGBG, R5F100LFGBG, R5F100LGGBG, R5F100LHGBG, R5F100LJGBG

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
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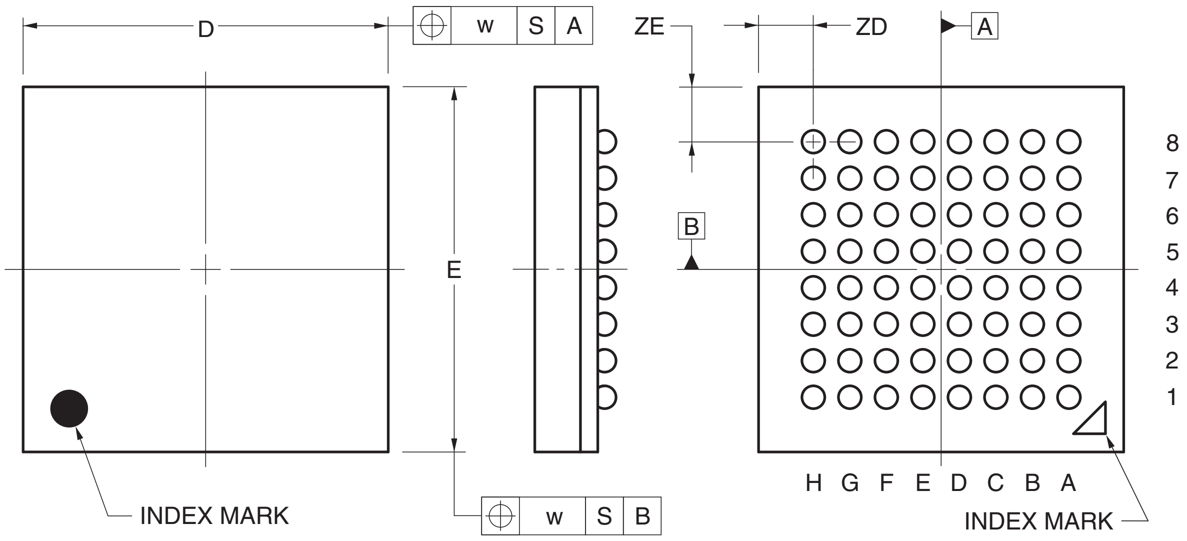

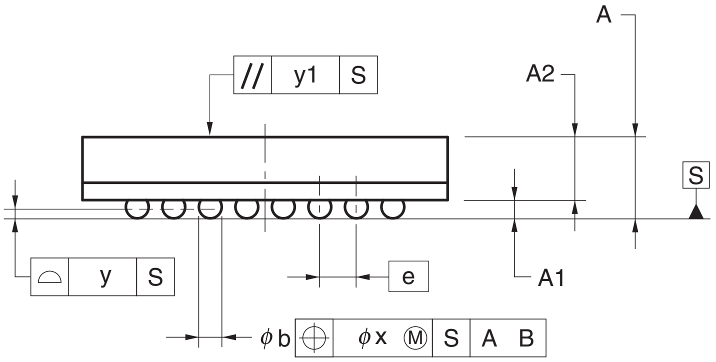

(UNIT:mm)

ITEM	DIMENSIONS
D	4.00±0.10
E	4.00±0.10
w	0.15
A	0.89±0.10
A1	0.20±0.05
A2	0.69
e	0.40
b	0.25±0.05
x	0.05
y	0.08
y1	0.20
ZD	0.60
ZE	0.60

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Rev.	Date	Description	
		Page	Summary
3.00	Aug 02, 2013	163	Modification of table in (8) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I^2C mode) (1/2)
		164, 165	Modification of table, note 1, and caution in (8) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I^2C mode) (2/2)
		166	Modification of table in 3.5.2 Serial interface IICA
		166	Modification of IICA serial transfer timing
		167	Addition of table in 3.6.1 A/D converter characteristics
		167, 168	Modification of table and notes 3 and 4 in 3.6.1 (1)
		169	Modification of description in 3.6.1 (2)
		170	Modification of description and note 3 in 3.6.1 (3)
		171	Modification of description and notes 3 and 4 in 3.6.1 (4)
		172	Modification of table and note in 3.6.3 POR circuit characteristics
		173	Modification of table of LVD Detection Voltage of Interrupt & Reset Mode
		173	Modification from Supply Voltage Rise Time to 3.6.5 Power supply voltage rising slope characteristics
		174	Modification of 3.9 Dedicated Flash Memory Programmer Communication (UART)
		175	Modification of table, figure, and remark in 3.10 Timing Specs for Switching Flash Memory Programming Modes
3.10	Nov 15, 2013	123	Caution 4 added.
		125	Note for operating ambient temperature in 3.1 Absolute Maximum Ratings deleted.
3.30	Mar 31, 2016		Modification of the position of the index mark in 25-pin plastic WFLGA (3 × 3 mm, 0.50 mm pitch) of 1.3.3 25-pin products
			Modification of power supply voltage in 1.6 Outline of Functions [20-pin, 24-pin, 25-pin, 30-pin, 32-pin, 36-pin products]
			Modification of power supply voltage in 1.6 Outline of Functions [40-pin, 44-pin, 48-pin, 52-pin, 64-pin products]
			Modification of power supply voltage in 1.6 Outline of Functions [80-pin, 100-pin, 128-pin products]
			$\overline{\text{ACK}}$ corrected to ACK
			$\overline{\text{ACK}}$ corrected to ACK

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